L Number			DB	Time stamp
-	768	1 (I and I and I and I active near (I avel of replan or	HSPAT.	2002/06/14 16:9
	1	medium or film)) and (quantum near well or gw) and (mirror or (flow	US-PGPUB;	2002/00/14 10.2
		and high) near reflect\$)) and \$72/\$	EPO; JPO;	
		"	DERWENT	
				;
-	260	((semiconductor near laser) and (active near (layer or region or	IBM_TDB	
		medium or film) and (quantum near mall a constant of the const	USPAT;	2001/11/29 18:0
		medium or film)) and (quantum near well or qw) and (mirror or ((low		
		and high) near reflect\$)) and \$72/\$) and \$72/96	EPO; JPO;	İ
			DERWENT	
-			IBM_TDB	
	11	(((semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 18:0
		medium or film)) and (quantum near well or qw) and (mirror or ((low	US-PGPUB;	
		and high) near reflect\$)) and 372/\$) and 372/96) and (laminat\$ near	EPO; JPO;	
		structure)	DERWENT;	
_	4	(semiconductor near laser) and (active near (layer or region or	IBM_TDB	
		medium or film)) and (quantum near well or qw) and ((low and high)	USPAT;	2002/06/14 16:2
		near reflect\$) and 372/\$ and (laminat\$ near structure)	US-PGPUB;	
		and reflectly and 5/2/ \$ and (faminal \$ near structure)	EPO; JPO;	1
			DERWENT;	
		//	IBM_TDB	
-	4	((semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 18:1
		medium or film) SAME (quantum near well or gw)) and ((low and	US-PGPUB;	
		high) near reflect\$) and (laminat\$ near structure)) and 372/\$	EPO; JPO;	
		· ·	DERWENT;	
			IBM_TDB	
-	5	(semiconductor near laser) and (active near (layer or region or	T .	2001/11/25
		medium or film) SAME (quantum near well or qw)) and ((low and	USPAT;	2001/11/29 19:24
		high) near reflect\$) and (laminat\$ near structure)	US-PGPUB;	
		8 / = (minimato fical structure)	ЕРО; ЈРО;	
			DERWENT;	
-	73	(semiconductor mean learn) at 1/ //	IBM_TDB	
		(semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 19:27
		medium or film) SAME (quantum near well or qw)) and ((low and	US-PGPUB;	
		high) near reflect\$)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	1	(semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 19:27
		medium or film) SAME (quantum near well or gw)) and (low and	US-PGPUB;	2001/11/29 19:27
	į.	high) near mirror) and (laminat\$ near structure)	EPO; JPO;	
		,		
			DERWENT;	
Í	56	((semiconductor near laser) and (active near (layer or region or	IBM_TDB	
1	1	medium or film) SAME (quantum near well or qw)) and ((low and	USPAT;	2001/11/29 19:28
		high) near reflect\$)) and 372/\$	US-PGPUB;	
			EPO; JPO;	
	ĺ		DERWENT;	
	.	/	IBM_TDB	
	4	(semiconductor near laser) and (active near (layer or region or	USPAT;	2001/11/29 19:42
	1	medium or film) SAME (quantum near well or gw)) and ((low and	US-PGPUB;	
		high) near mirror)	EPO; JPO;	
	ļ		DERWENT;	
	1			
	1093	(semiconductor near laser) and (active near (layer or region or	IBM_TDB	
		medium or film)) and (quantum near well or qw) and (mirror or ((low	USPAT;	2002/06/14 16:36
		and high) near reflect\$)) and substrate	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
İ	100	(IBM_TDB	
	186	(semiconductor near laser) and (active near flaver or region or	USPAT;	2002/06/14 16:48
	1	medium or film)) and (quantum near well or gw) and (low near	US-PGPUB;	
			- ~ ~ ~ VL VL.	
	1			
	1	reflect\$5)and (high near reflect\$5) and substrate	EPO; JPO; DERWENT;	

-	113	((semiconductor near laser) and (active near (layer or region or	USPAT;	0000/00/11 17 27
		medium or film)) and (quantum near well or gw) and flow near	US-PGPUB:	2002/06/14 17:25
	1	reflect\$5)and (high near reflect\$5) and substrate) and cavity	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT:	
			IBM TDB	
_	63	((semiconductor near laser) and (active near (layer or region or	USPAT:	2002/06/14 17:26
		medium or film)) and (quantum near well or gw) and flow near	US-PGPUB;	1 11.20
		reflect\$5)and (high near reflect\$5) and substrate) and (cavity near2	EPO; JPO;	
		length)	DERWENT;	
_	40		IBM_TDB	
_	43	((semiconductor near laser) with (optical near fiber)) and (active near	USPAT;	2002/06/16 15:26
		(layer or region or medium or film)) and (quantum near well or qw)	US-PGPUB;	
		and ((low and high) near reflect\$) and substrate	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	